UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO. : 6,800,876 B2 : October 5, 2004 DATED

Page 1 of 1

INVENTOR(S) : Edmond et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title page,

Item [54] Title, reads "GROUP III NITRIDE LED WITH UNDOPED CLADDING LAYER (5000.137)" should read -- GROUP III NITRIDE LED WITH UNDOPED CLADDING LAYER AND MULTIPLE QUANTUM WELL --.

Item [75], Inventors, "Hua-shuang Kong" should read -- Hua-Shuang Kong --. Item [56], References Cited, U.S. PATENT DOCUMENTS, reads "5,670,798 A 9/1997 Kimura" should read -- 5,670,798 A 9/1997 Schetzina --, OTHER PUBLICATIONS, reads "Expert Report P-N Junction Location and Layer Conductivity in InGaN LED Chips Manufactured By"." reference, should read --

"Expert Report P-N Junction Location and Layer Conductivity in InGaN LED Chips Manufactured By Cree, Inc." --, "Expert Report Title: Structure and Analysis of InGan LED Chips Manufaced By"." reference, should read -- "Expert Report Title: Structure and Analysis of InGan LED Chips Manufacted by Cree Inc." --.

Column 15,

Line 12, "Group III" should read -- Group III --. Line 22, "where 0.I

Signed and Sealed this

Fourteenth Day of June, 2005

JON W. DUDAS Director of the United States Patent and Trademark Office